**Product data sheet** 

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a TO92 plastic package. This very sensitive gate "series D" triac is intended for interfacing with low power drivers including microcontrollers.

### 2. Features and benefits

- Direct interfacing to logic level ICs
- · Direct interfacing with low power gate drivers and microcontrollers
- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Very sensitive gate
- · Triggering in all four quadrants

### 3. Applications

- Air conditioner indoor fan control
- General purpose low power motor control
- · General purpose switching and phase control

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Absolute	maximum rating						
$V_{DRM}$	repetitive peak off-state voltage			-	-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 51.2 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>		-	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5		-	-	12.5	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$		-	-	13.7	Α
T <sub>j</sub>	junction temperature			-	-	125	°C
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$		-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G+;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$		-	-	7	mA

I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.3	10	mA
$V_T$	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 k $\Omega$	20	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; dI_{com}/dt = 0.5 \text{ A/ms};$ $I_T = 1 \text{ A}; gate open circuit}$	3	-	-	V/µs

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		
2	G	gate	1,1,1,1	T2—T1
3	Т1	main terminal 1	1	sym051

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT131-600D	TO92	BT131-600D,412	Bulk	1000	SOT54	14-Nov-2013
BT131-600D	TO92	BT131-600DQP	Reel	2000	SOT54	14-Nov-2013
BT131-600D/L01	TO92	BT131-600D/L01EP	Bulk	500	SOT54/L01	14-Nov-2013

## 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BT131-600D	131-6D

# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 51.2 °C; <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig 4; Fig 5	-	12.5	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	13.7	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN	-	0.78	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 10 mA	-	50	A/µs
		I <sub>G</sub> = 10 mA	-	50	A/µs
		I <sub>G</sub> = 14 mA	-	10	A/µs
		I <sub>G</sub> = 10 mA	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_GM$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

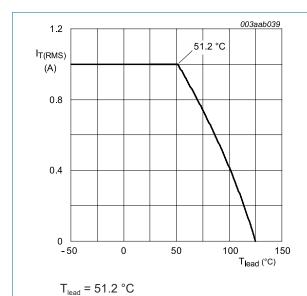


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

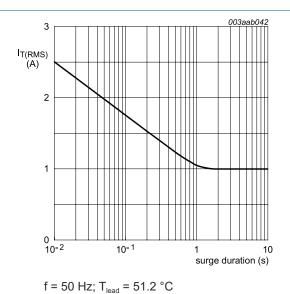


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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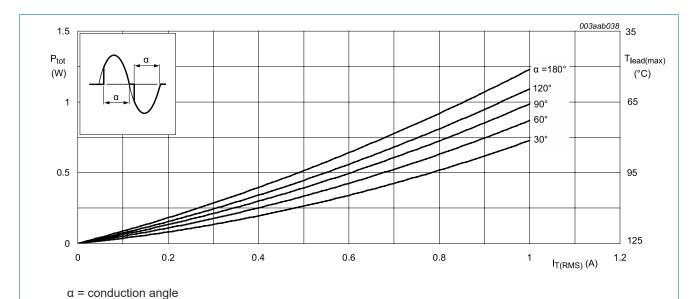
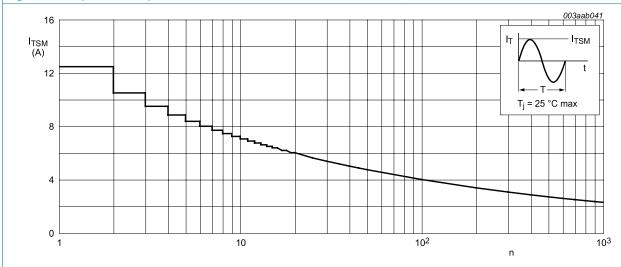
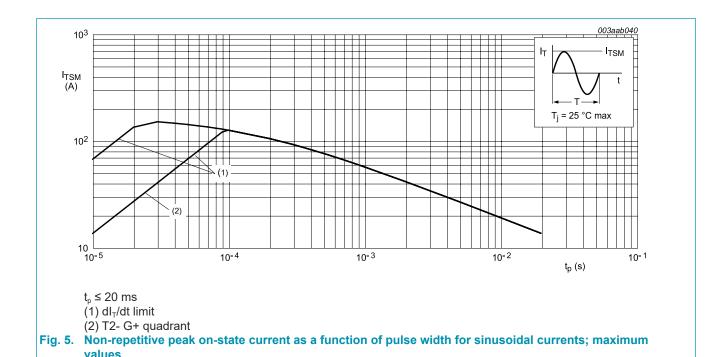


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

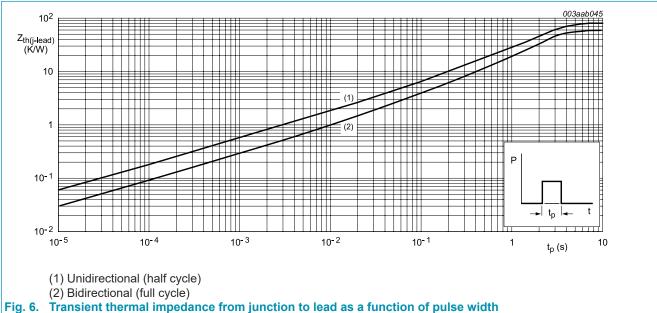
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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

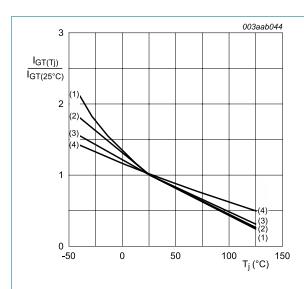
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance	full cycle; Fig 6	-	-	60	K/W
	from junction to lead	half cycle; <u>Fig 6</u>	-	-	80	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					'
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	7	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	10	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; Fig. 9$	-	1.3	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V <sub>GT</sub> gate trigger voltage		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C}$	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 kΩ	20	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 125 °C; $dI_{com}/dt$ = 0.5 A/ms; $I_T$ = 1 A; gate open circuit	3	-	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 1.5 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

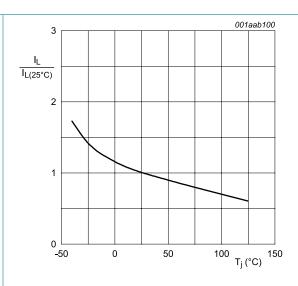


Fig. 8. Normalized latching current as a function of junction temperature

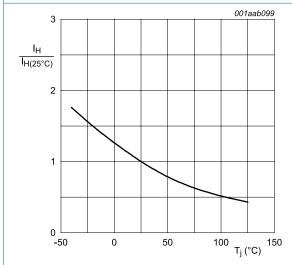
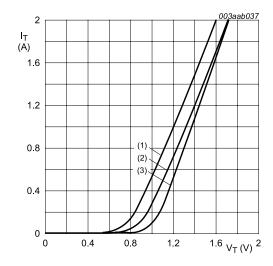


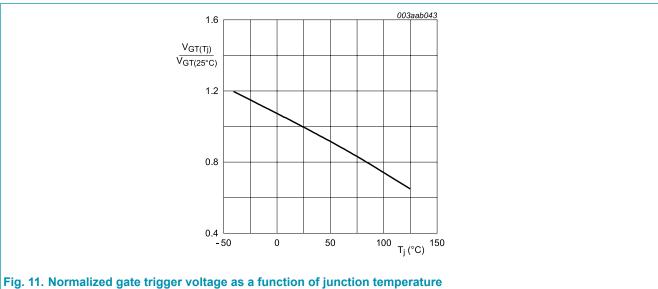
Fig. 9. Normalized holding current as a function of junction temperature



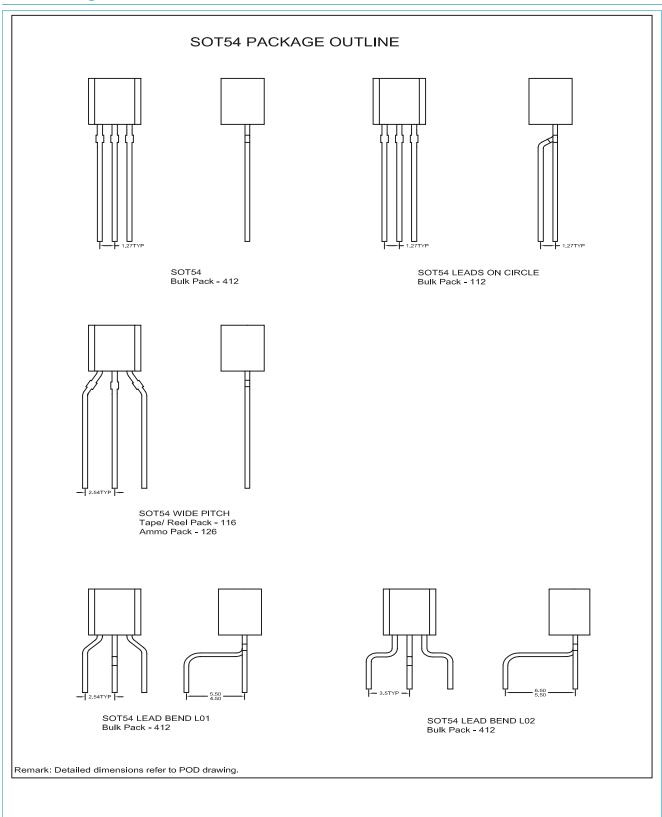
- $V_o$  = 0.92 V;  $R_s$  = 0.4  $\Omega$  (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

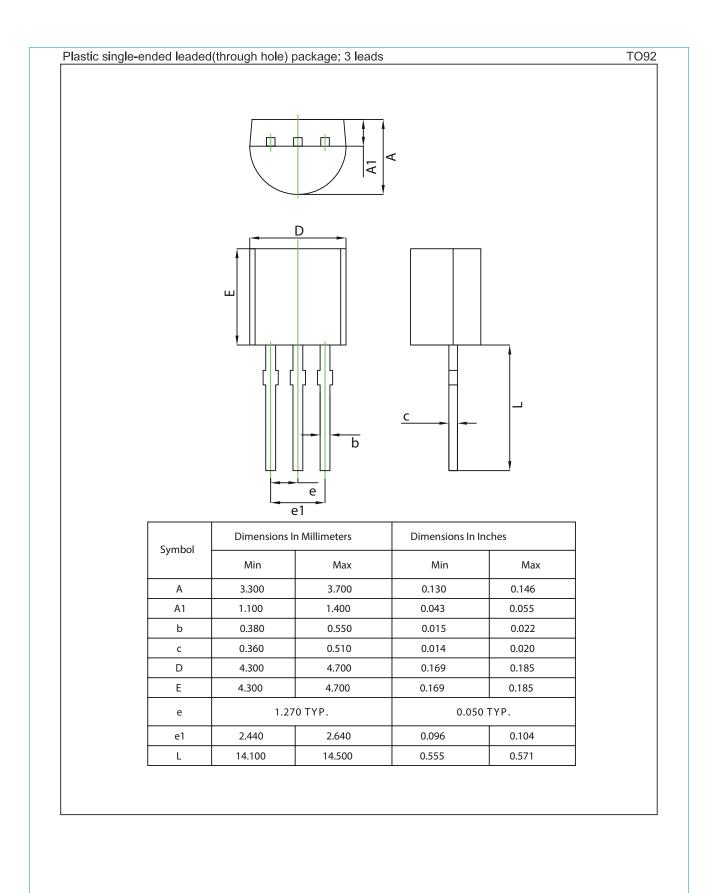
Fig. 10. On-state current as a function of on-state voltage

**WeEn Semiconductors** BT131-600D



# 11. Package outline





### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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**4Q Triac** 

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